



浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

产品规格书

Specification of products

产品名称：快恢复二极管

产品型号：MURP2001200

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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拟制	审核	核准
林益龙	曹剑龙	宗瑞

Ultra-Fast Soft Recovery Diode Module

Description

Ultra-FRD module devices are optimized to reduce losses and EMI/RFI in high frequency power conditioning electrical systems. These diode modules are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses

Features

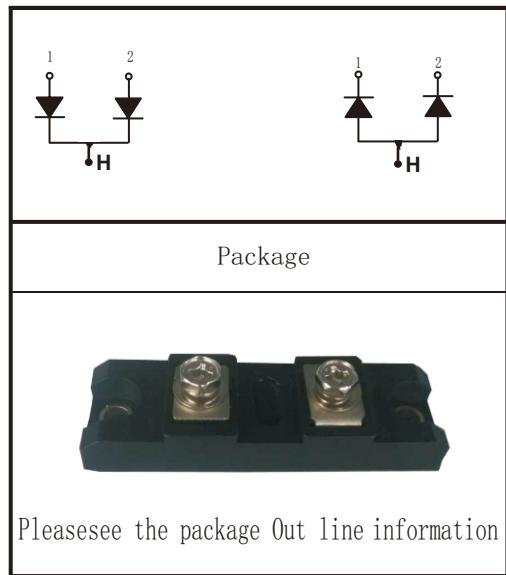
- ↪ Repetitive Reverse Voltage V_{RRM} = 1200V
- ↪ Low Forward Voltage Drop VF (typ.)= 1.2V
- ↪ Average Forward Current I_F (AV.) = 200A @ $T_c= 100^\circ\text{C}$
- ↪ Ultra-Fast Reverse Recovery Time : t_{rr} (typ.) = 130 ns
- ↪ Extensive Characterization of Recovery Parameters
- ↪ Reduced EMI and RFI
- ↪ Non Isolation Type Package

Applications

Motor Drives, Free wheel use, High Power Converters Welders Various Switching and Telecommunication Power Supply.

Equivalent Circuit and Package

Equivalent Circuit



Please see the package Out line information

Absolute Maximum Ratings @ $T_j = 25^\circ\text{C}$ (Per Leg)

Symbol	Parameter	Conditions	Ratings	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		1200	V
$V_{R(DC)}$	Reverse DC Voltage		320	V
I_F (AV)	Average Forward Current @ $T_c= 25^\circ\text{C}$ @ $T_c= 100^\circ\text{C}$	Resistive Load	400 200	A A
I_{FSM}	Surge (non-repetitive) Forward Current	One Half Cycle at 60Hz, Peak Value	3300	A
I_t^2	I^2t for Fusing	Value for One Cycle Current, $t_w= 8.3\text{ms}$, $T_j= 25^\circ\text{C}$ Start	45.0×10^3	$\text{A}^2 \text{ s}$
T_j	Junction Temperature		-40 ~ 125	$^\circ\text{C}$
T_{stg}	Storage Temperature		-40 ~ 125	$^\circ\text{C}$
P_d	Maximum Power Dissipation		700	W
-	Mounting Torque		4.0	N.m
-	Terminal Torque		3.0	N.m



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Thermal Characteristics

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
R _{th(j-c)}	Thermal Resistance	Junction to Case	-	-	0.15	°C/W

Electrical Characteristics @T_j=25°C (unless otherwise specified)

Symbol	Parameter	Conditions	Values			Unit	
			Min.	Typ.	Max.		
V _R	Cathode Anode Breakdown Voltage	I _R = 100uA	1200	-	-	V	
V _{FM}	Maximum Forward Voltage	I _{FM} = 200A, T _c = 25°C	-	1.2	1.5	V	
		I _{FM} = 200A, T _c = 100°C	-	1.0	1.2	V	
I _{RRM}	Repetitive Peak Reverse Current	T _C = 100°C, V _{RRM} applied	-	-	8.5	mA	
T _{rr}	Reverse Recovery Time	I _{FM} = 200A, V _R = 300V di/dt = -100A/us	T _c = 25°C	-	130	150	ns
			T _c = 100°C	-	180	-	ns

Rating and Characteristic

Performance Curves

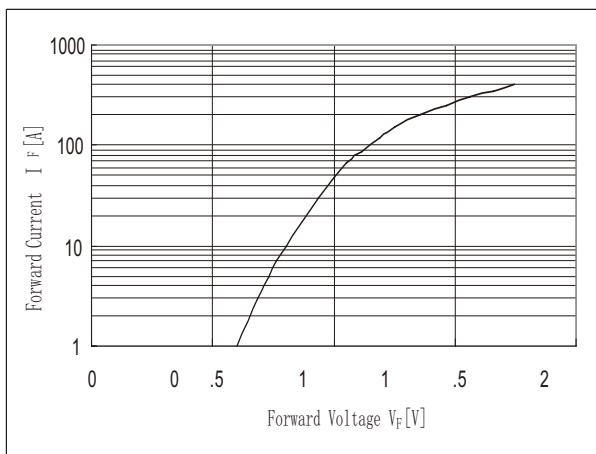


Fig. 1 : Typical Forward Voltage Drop
vs. Instantaneous Forward Current

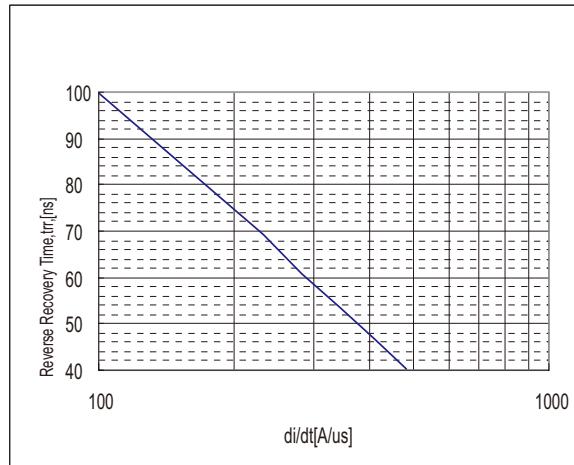


Fig. 2 : Typical Reverse Recovery Time
vs. $-di/dt$

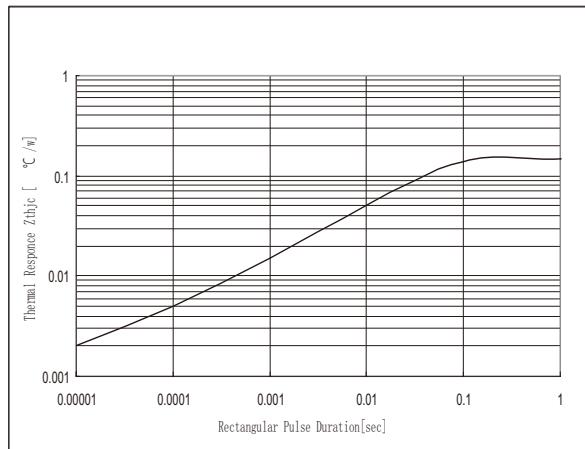


Fig. 3 : Transient Thermal Impedance (Z_{thjc})
Characteristics

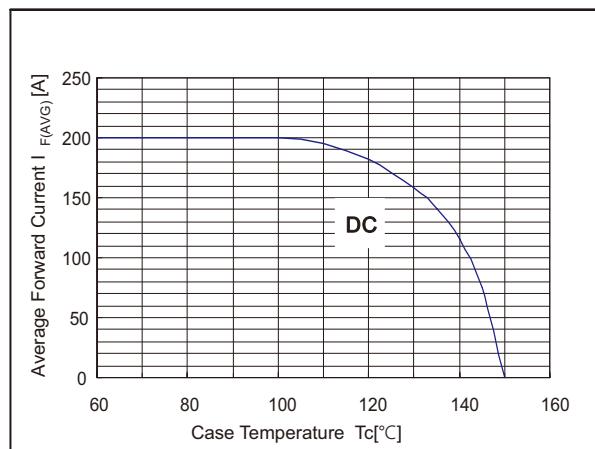


Fig. 4 : Forward Current Derating Curve

Outside Dimension

